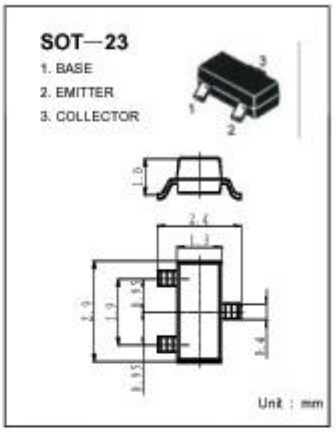
SOT-23 Plastic-Encapsulate Transistors

MMBT4401LT1 TRANSISTOR（NPN）



FEATURES

Power dissipation

P_{CM} : 0.3 W （Tamb=25℃）

Collector current

I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100 μA, I_E=0	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1mA, I_B=0	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100 μA, I_C=0	6		V
Collector cut-off current	I_{CBO}	V_{CB}=50 V, I_E=0		0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=35 V, I_B=0		0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0		0.1	μA
DC current gain	$H_{FE\ (1)}$	V_{CE}=1 V, I_C= 150mA	100	300	
	$H_{FE\ (2)}$	V_{CE}=2 V, I_C= 500mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=150 mA, I_B=15mA		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= 150 mA, I_B=15mA		0.95	V
Transition frequency	f_T	V_{CE}= 10V, I_C= 20mA f = 100MHz	250		MHz

DEVICE MARKING: MMBT4401LT1=2X